

APPENDIX

VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS:

Claim 1 is amended as follows:

1. (Amended) A group III nitride compound semiconductor device of a successively laminated structure comprising:

a substrate;

a buffer layer;

a first layer formed of $\text{In}_x\text{Ga}_{1-x}\text{N}$ ($0 < x < 1$); and

a second layer formed of $\text{In}_y\text{Ga}_{1-y}\text{N}$ ($0 < y < 1$, $y \neq x$);

wherein a composition ratio of In in said first layer is changed continuously or intermittently in a direction toward the second layer side from the buffer layer side so that a composition of said first layer in a face brought into contact with said second layer becomes substantially equal to a composition of said second layer.

End of Appendix.